

A'
cont'd

602 extends beyond the left edge of region 406 while the right end of island 602 is proximate the right edge of region 406 but within region 406. Island 604 is non-symmetrically disposed relative to island 602 in that the right end of island 604 extends beyond the right edge of region 406 while the left end of island 604 is within region 406. Thus, islands 602 and 604 are non-symmetric about axis A-A' and axis B-B'.

IN THE CLAIMS:

Please amend claim 1, and add new claims 101-103, as follows:

52b' /
A2

1. (Amended) An electrostatic discharge (EDS) protection device, comprising:
a semiconductor layer;
a first diffusion region formed in the layer;
a second diffusion region formed in the layer adjacent to and spaced apart from the first diffusion region;
a channel region formed between the first and second diffusion regions; and
at least one island formed in the first diffusion region, the at least one island being positioned non-symmetrically with respect to a symmetry axis, wherein
said symmetry axis extending from a midpoint of the channel region perpendicular to the channel region and in parallel to a surface of the semiconductor layer.

22b' / A3

--101. (New) The ESD protection device of claim 1, wherein
said channel region is bounded by first and second diffusion edges of the first diffusion region;

Sub 3-1
Cont'd

said at least one island having a first island edge near said first diffusion edge and a second island edge near said second diffusion edge;

a first gap of at least zero spacing between the first diffusion edge and a first nearest island edge;

a second gap of at least zero spacing between the second diffusion edge and a second nearest island edge; and said first gap being larger than the second gap.

102. (New) An electrostatic discharge (ESD) protection device, comprising:

A3
cont'd

a semiconductor layer;

a first diffusion region formed in the layer;

a second and a third diffusion region formed in the layer each adjacent to and spaced apart from the first diffusion region;

a first channel formed between the first and second diffusion regions;

a second channel formed between the first and third diffusion regions;

a contact array comprising at least one contact formed over the first diffusion region for providing conductive contact to the first diffusion region;

a first group of at least one island disposed in the first diffusion region between the contact array and the first channel;

a second group of at least one island disposed in the first diffusion region between the contact array and the second channel,

wherein said first and second groups include all islands in the first diffusion region and said first and second groups being disposed non-symmetrically with respect

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